

# Enabling High Performance Instruments for UV Astronomy and Space Exploration with ALD

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# Outline

- Introduction to Jet Propulsion Laboratory
- Overview of Applications and Results
  - Anti-reflective coatings
  - Optical elements (mirrors/filters)
  - Surface treatments and passivation
- Conclusions and acknowledgements

# Jet Propulsion Laboratory



- JPL is a child of Caltech: founded in 1936 as a graduate student project under Professor Theodore von Kármán.
- JPL led the development of US rocket technology in WWII.
- Developed the first U.S. satellite, Explorer I.
- JPL was transferred to NASA upon its creation in 1958.
- JPL spacecraft have explored all the planets of the solar system except Pluto.

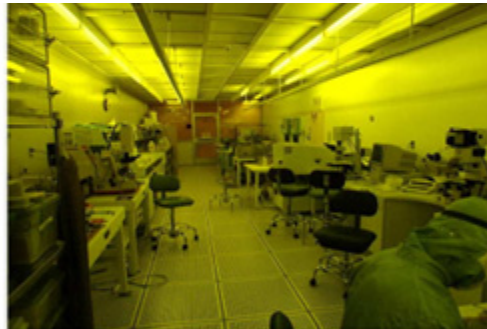
- About JPL:
  - A Federally-Funded Research and Development Center (FFRDC) under NASA sponsorship;
  - A division of Caltech, staffed with > 5000 Caltech employees;
  - JPL Director is a Vice-President of Caltech.
- Programs:
  - NASA programs;
  - Defense programs and civilian programs of national importance compatible with JPL capabilities.



# Microdevices Laboratory



- MDL Facility built in 1989 to provide end-to-end capabilities for advanced electronic materials, device fabrication and characterization.
- Class 10–1,000 cleanrooms with e-beam & optical lithography, materials growth & deposition, wet & dry etching, thermal processing, optical/structural/electronic characterization capabilities for detector devices.
- Nom. \$ 30M of equipment investments are housed within MDL with 74 major pieces of Central Processing Equipment.
- Chartered to carry out innovative research and technology development for NASA applications and deliver instruments and components to flight applications
- Recent deliveries include superconducting detectors for the Herschel SPIRE and the Planck High Frequency Instrument that was launched by ESA in 2009





# Applications of UV Detectors

- Spectroscopy to investigate planetary atmospheres
  - Detection of Ozone (biomarker)
- Imaging and Spectroscopy for Astronomy and Cosmology
  - *e.g.* Galaxy Evolution Explorer (GALEX)
  - Star formation/Dark Energy studies
- Imaging for biomedical applications, Criminal investigations, and defense
  - Tumors
  - Bite marks/bruises
  - Rocket plumes

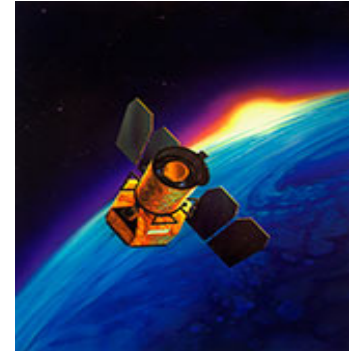
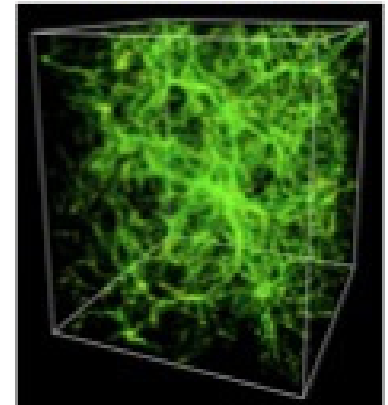
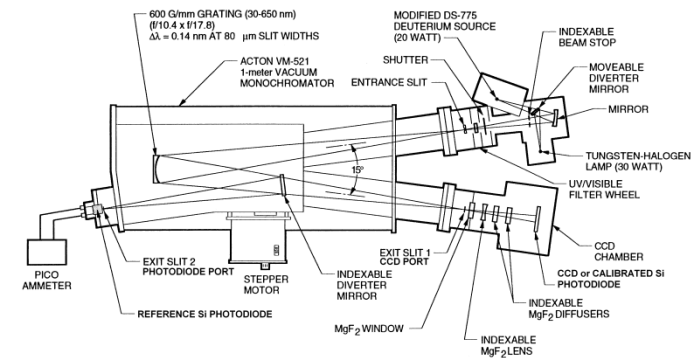


Illustration of GALEX and a proposed map of intergalactic medium



# CCD Characterization

- Characterization of absolute quantum efficiency of detectors is very difficult in the UV
  - Atmospheric absorption occurs in wavelengths  $< 160\text{nm}$
  - Silicon CCDs must be cooled to liquid nitrogen temperatures to reduce dark current
  - Quantum yield (electrons/photon) is greater than 1 for short wavelengths
- JPL has developed a system and methodology for these tests in our laboratory for rapid feedback during detector development and flight qualification\*



\*B.C. Jacquot, S.P. Monacos, M.E. Hoenk, F. Greer, T.J. Jones, and S. Nikzad, *Rev Sci. Instr.* 2011

# Delta doping technology as the ideal Back Illumination solution

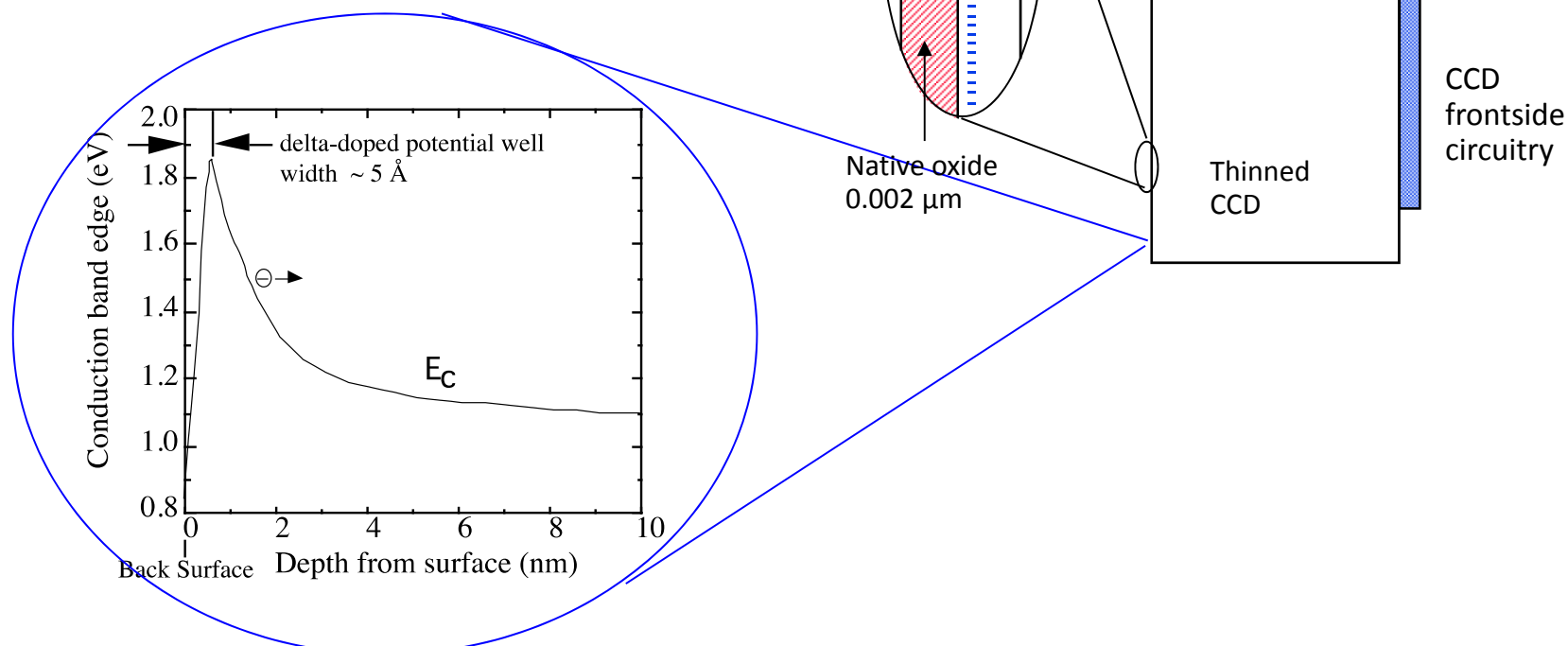


Bandstructure engineering for optimum performance

**Atomic layer control** over device structure

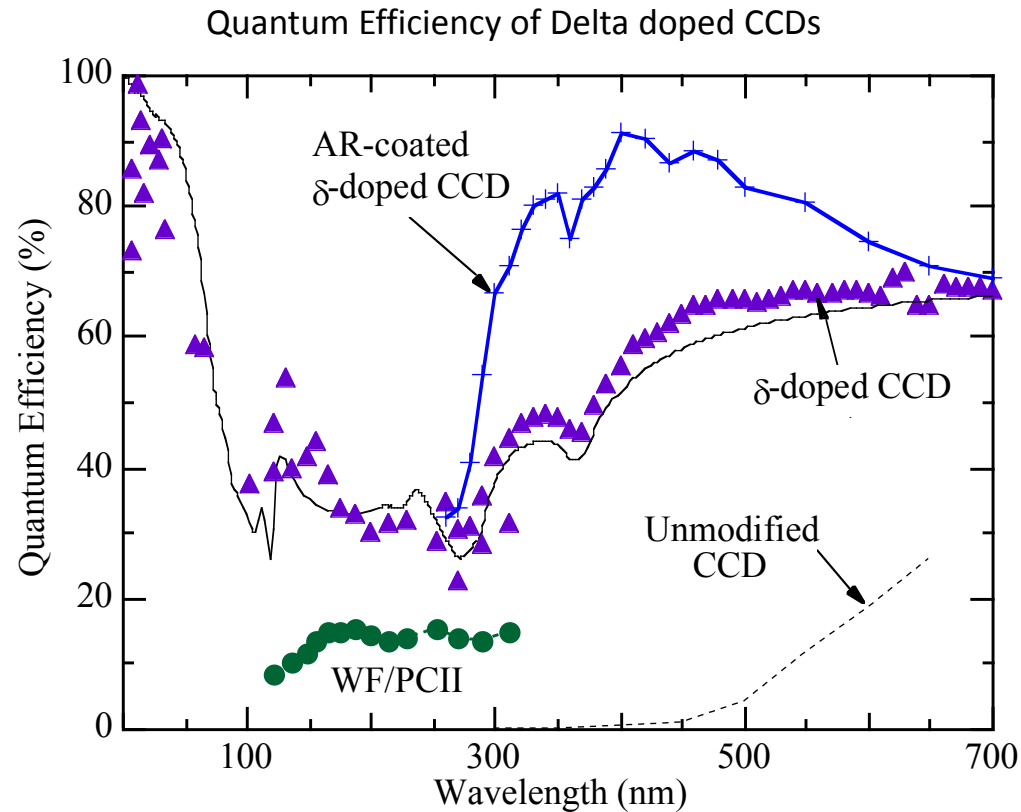
Low temperature process, compatible with VLSI, fully fabricated devices (CCDs, CMOS, PIN arrays)

Hoenk et al., *Applied Physics Letters*, **61**: 1084 (1992)



Fully-processed devices are modified using Molecular Beam Epitaxy (MBE)

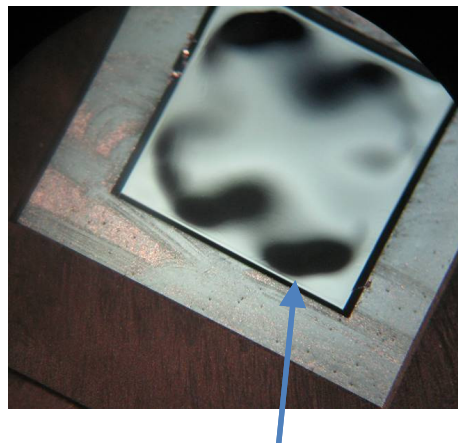
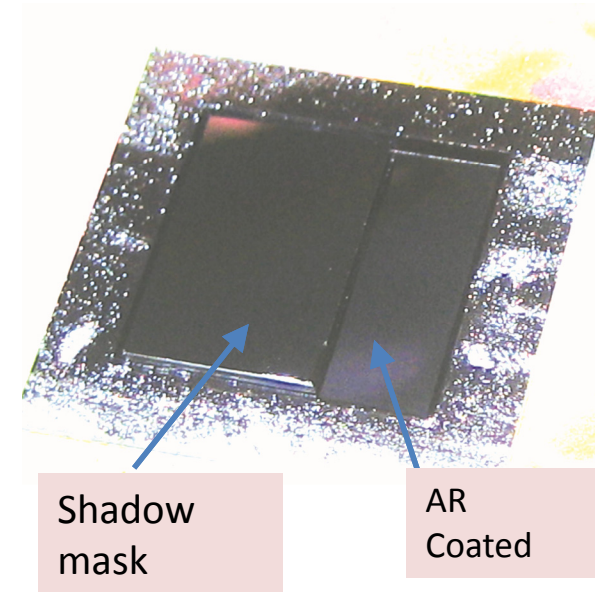
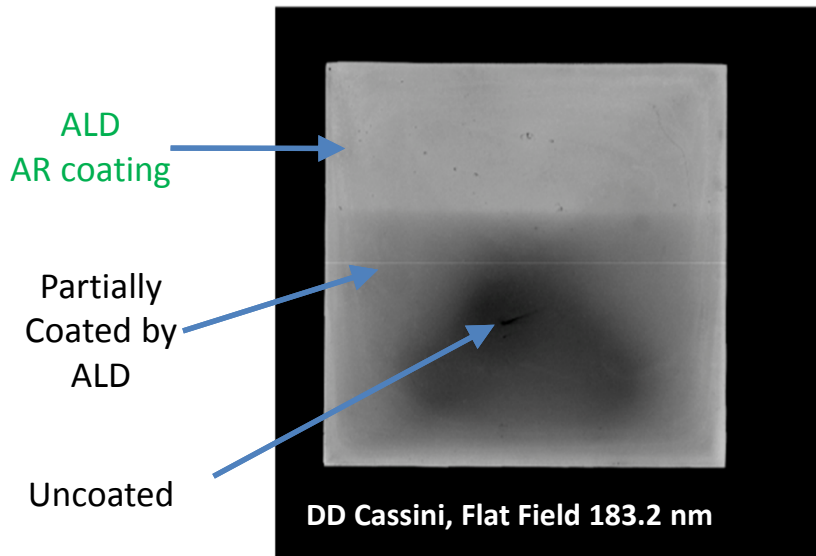
# High QE with Delta doping Technology



- 100% internal quantum efficiency, uniform, and stable (QY has been removed so maximum QE is 100%).
- Extreme UV measurements were made at SSRL
- Compatible with AR and filter coating: response can be tailored for different regions of the spectrum



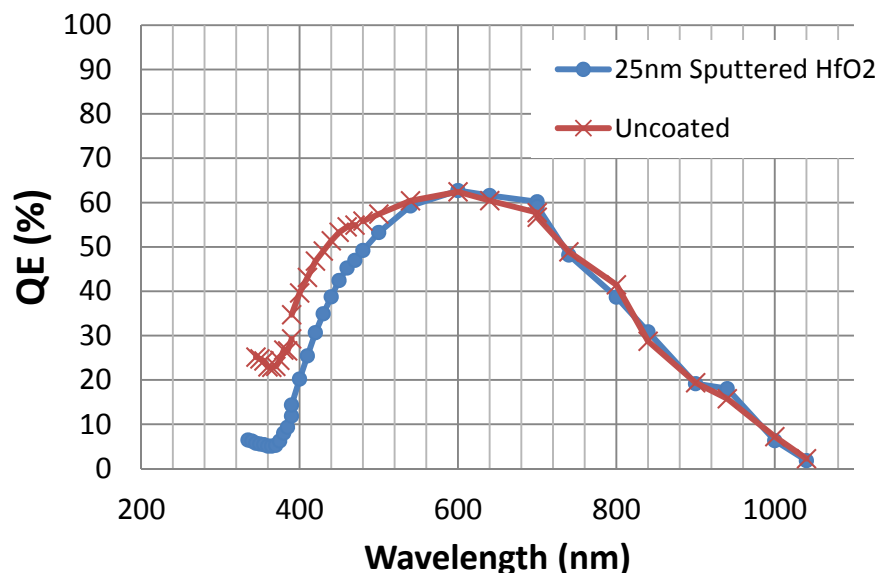
# Anti-Reflective Coatings for UV Astronomy



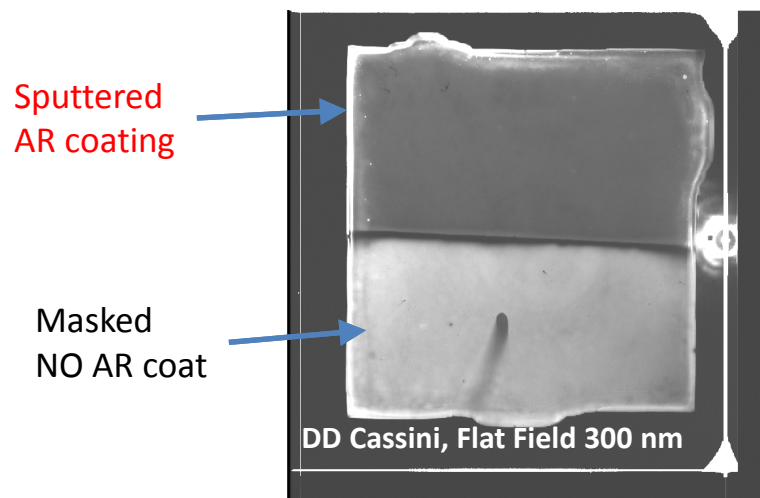
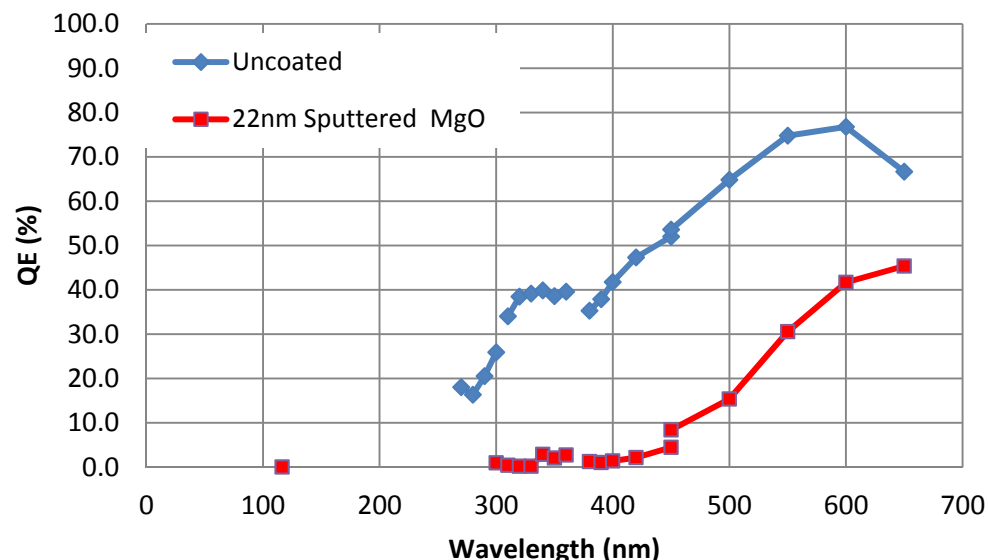
- AR Coatings used to enhance quantum efficiency of silicon detectors.
  - Many different materials needed for UV detection due to adsorption
  - Brighter → Higher QE
- Shadow masking used to ensure internal standard for comparison
  - Shadow masking is somewhat difficult due to conformality of the ALD coating process
  - Mask does not sit flat on unsupported membrane

# Sputtered anti-reflective coatings

Quantum Efficiency, Partially Coated



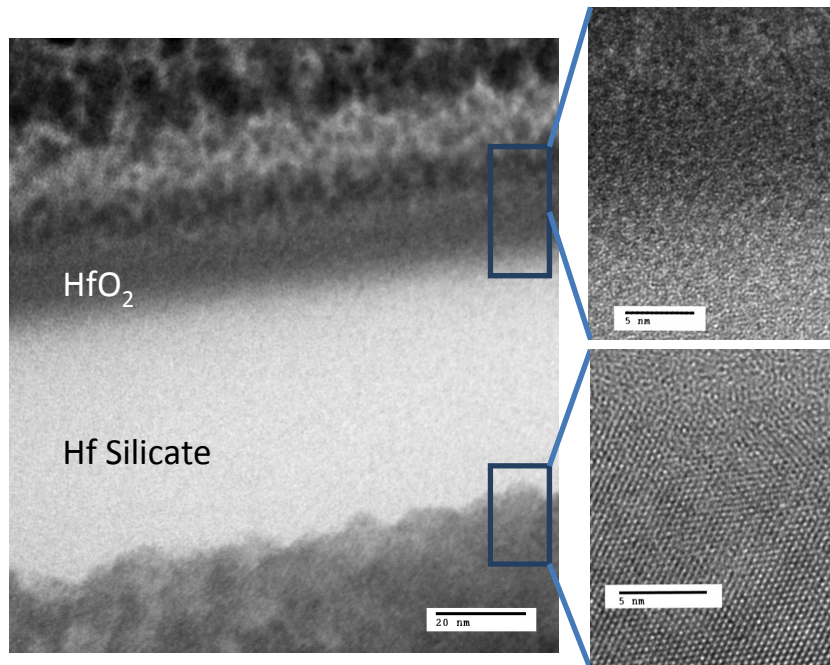
Quantum Efficiency - Delta Doped, Partial AR Coating



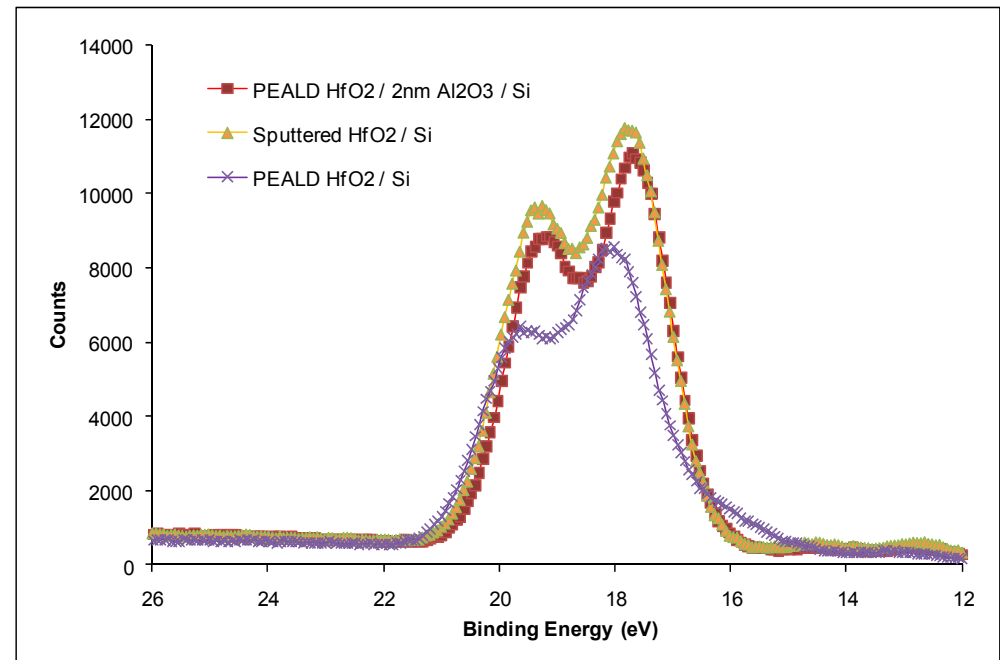
• Atomic Layer Deposition yields ***superior AR coating performance compared to sputtered films***

- Sputtered film QE far below that of uncoated reference
- Various materials analysis techniques used to investigate this result

TEM of PEALD  $\text{HfO}_2$  directly on Si

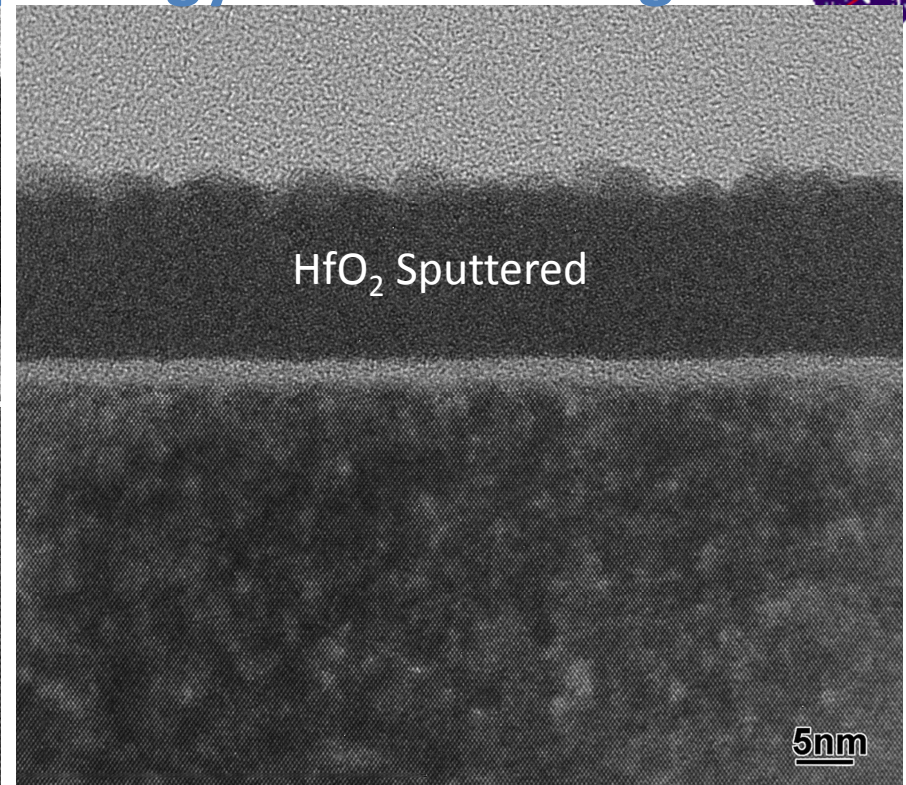
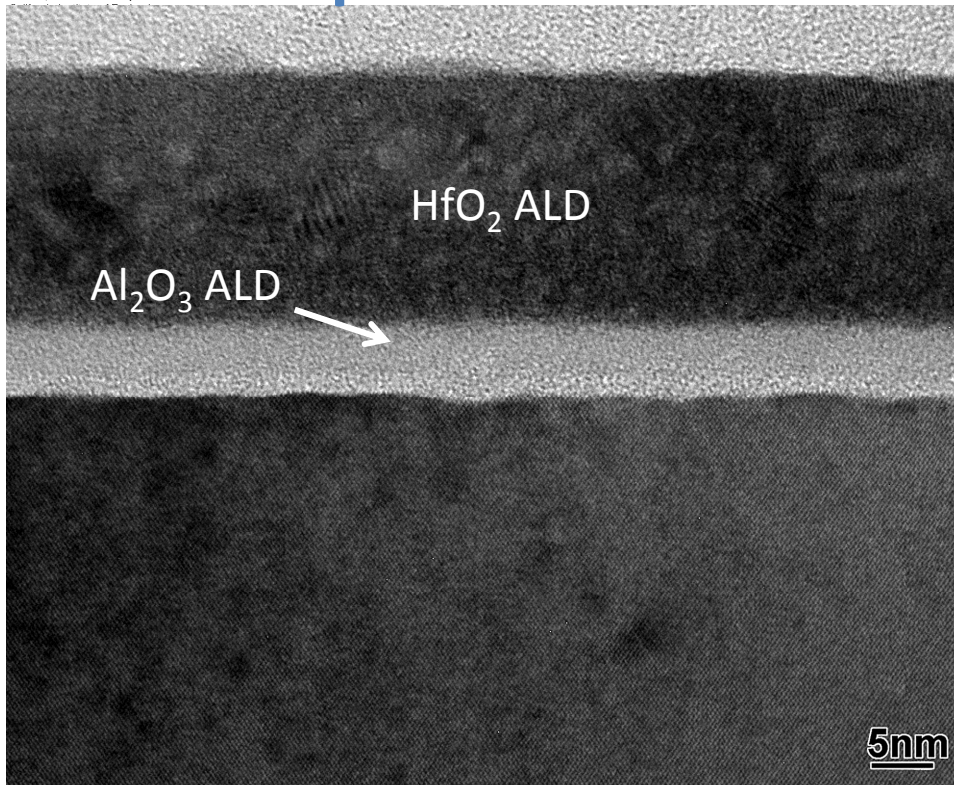


XPS Data from initial AR coating growth



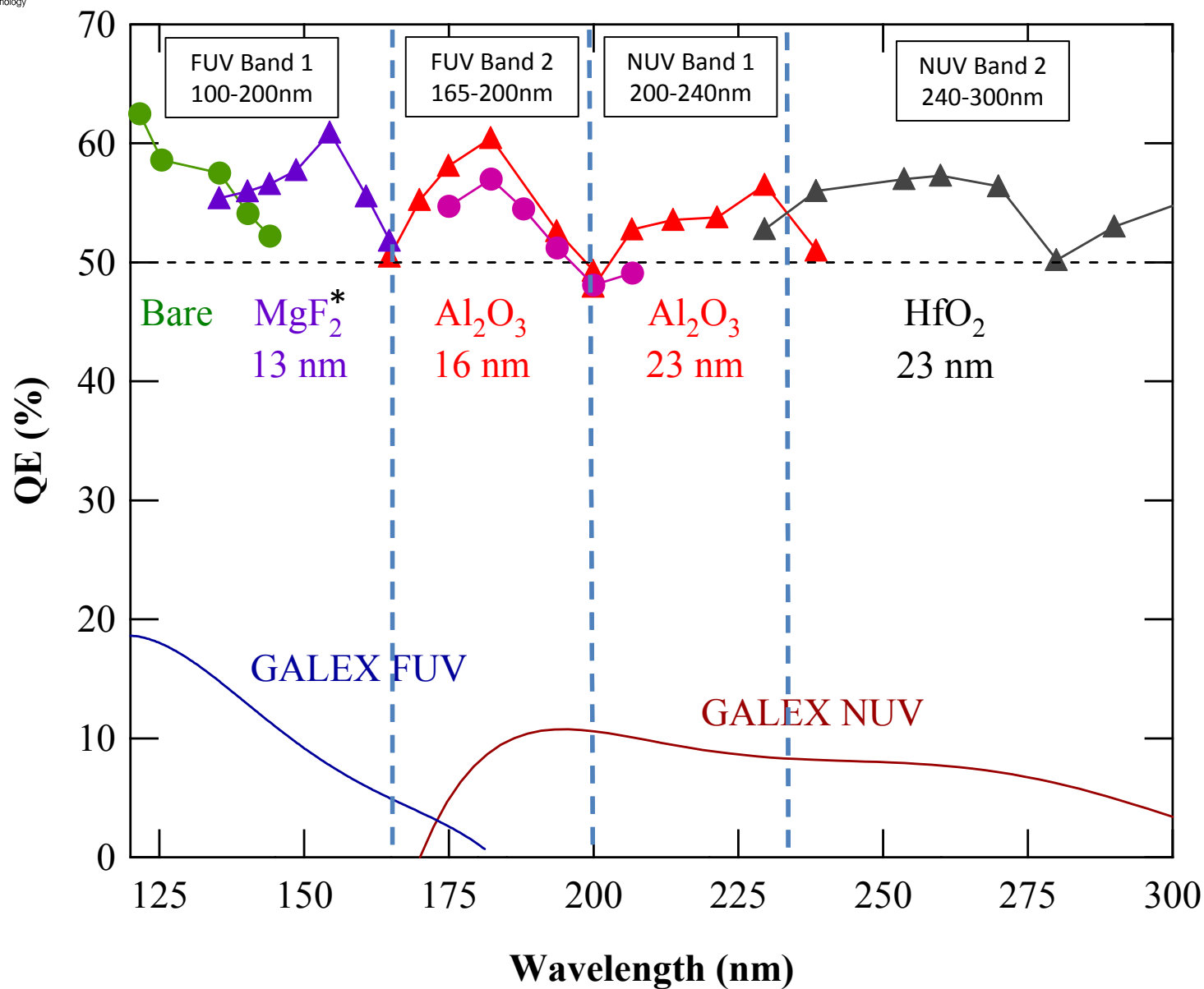
- Chemical interaction of ALD coating with substrate is possible.
- ALD bilayers were utilized to successfully mitigate this effect





- ALD AR coating Stack (Left) is significantly better than the Sputtered AR coating (right)
  - ALD is more dense (darker in the image)
  - ALD is smoother (potentially less scatter)
  - ALD is partially crystalline
- ALD AR coating technique allows for multilayers with sharp interfaces
  - Provides for optically transparent chemical barriers between films ( $\text{Al}_2\text{O}_3$  film at left)
  - Can create band pass filters or AR coatings that are highly tailored to a specific wavelength
- ALD AR coating technique has atomic layer precision
  - Enables sub-nanometer control over film thickness, which is important for UV AR coatings as  $<2\text{nm}$  thickness change impacts the performance

# Quantum Efficiency of FUV-NUV Bands

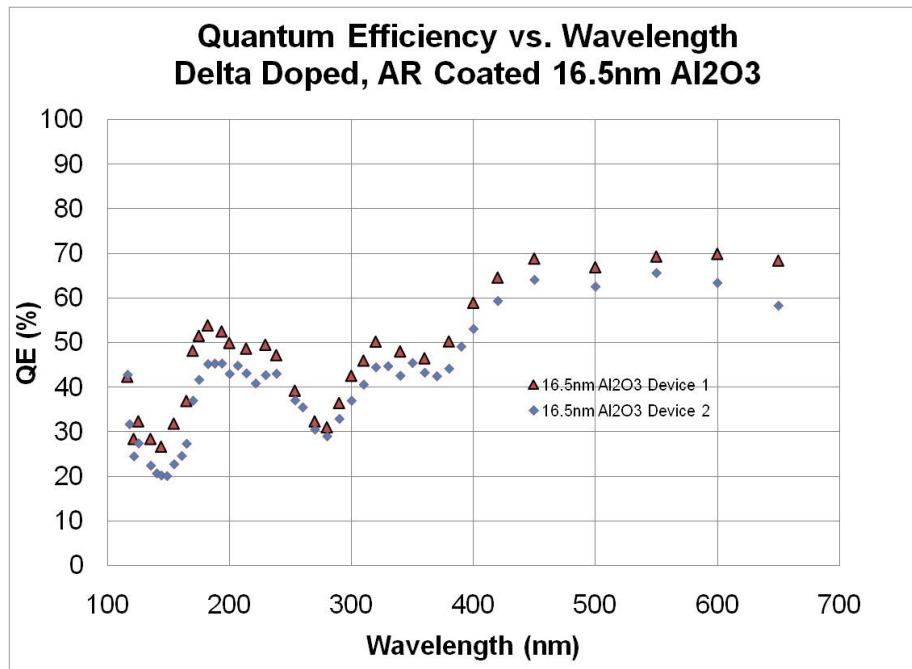


\*MgF<sub>2</sub> result  
for thermally  
evaporated film

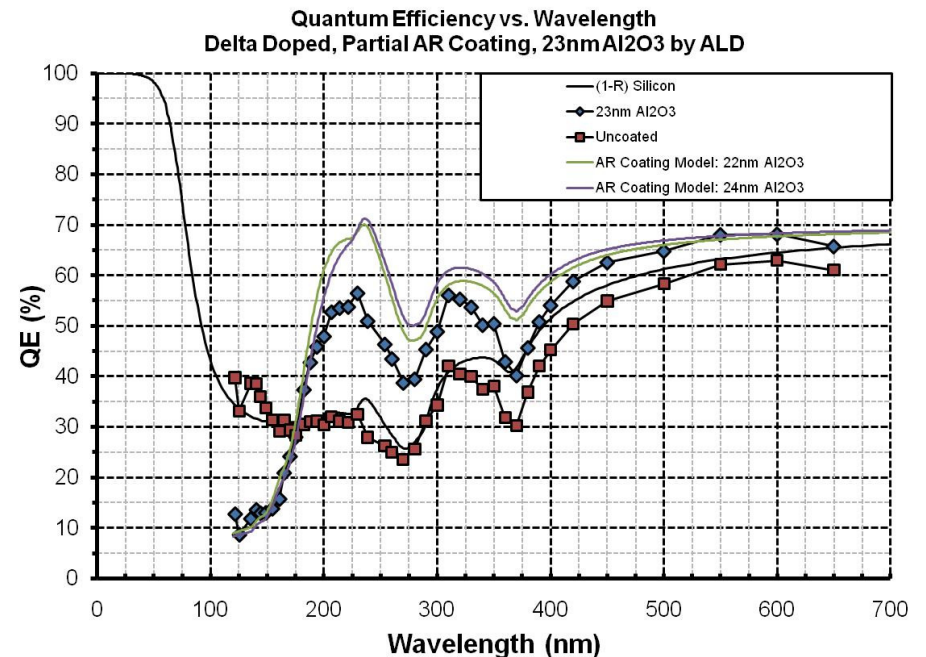
Atomic Layer Deposition AR coatings provide up to **2X improvement** over uncoated baseline and a **5x-50x improvement** over incumbent UV detector technology



# ALD Enables Atomic Control of Coatings



Same exact recipe run on JPL ALD system on two different devices separated by *a month*

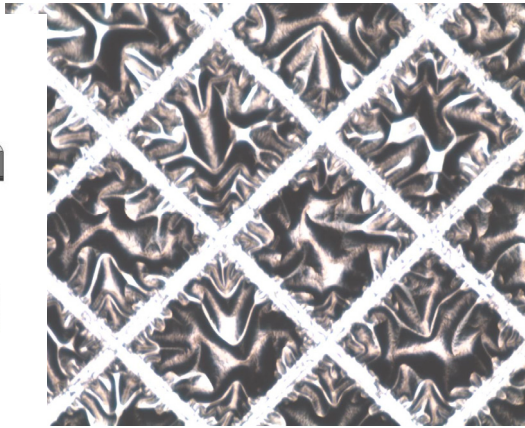
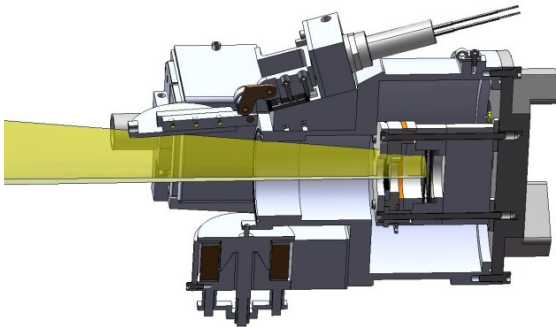


Wavelength dependence of coating performance *correctly predicted* by AR coating models based on precision UV ellipsometry measurements

- Reproducibility and accuracy of the ALD technique enables rational design and fabrication of anti-reflective coatings at the nanometer scale
- Multilayers feasible when required to prevent interactions or to provide for integrated filters (e.g. bandpass)

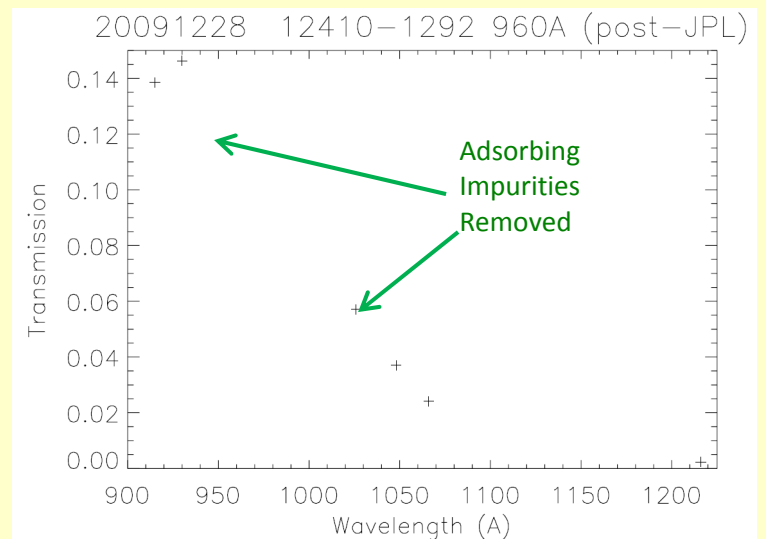
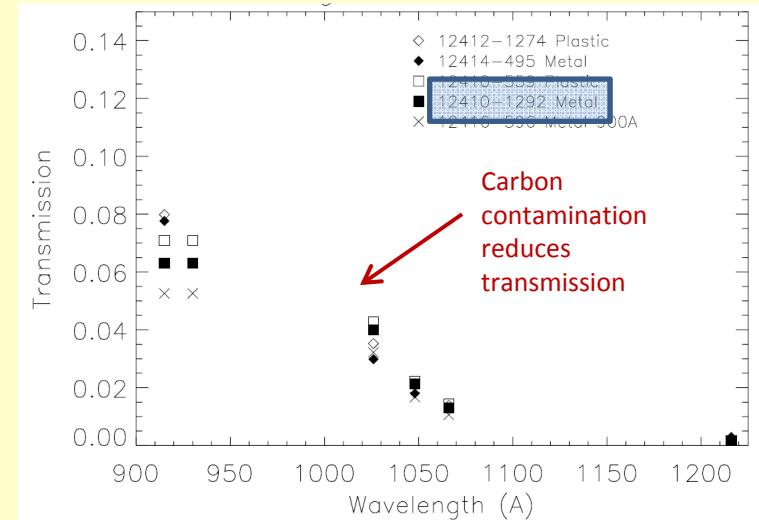
# UV Filter Enhancement/Fabrication

## FIRE telescope



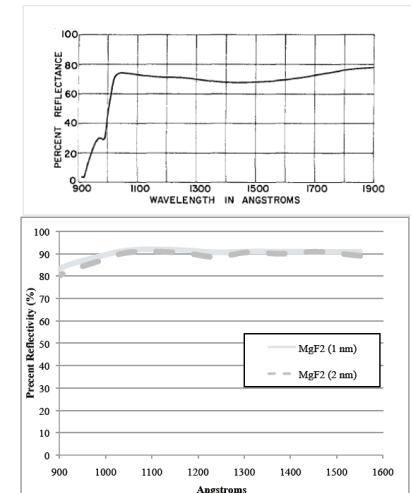
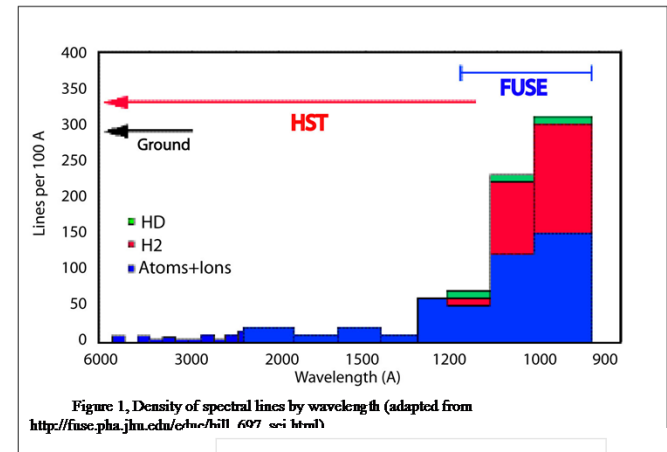
Indium foil on Ni mesh

- FIRE Telescope objective to image the very hottest stars, with no interference from Lyman alpha
  - Thin Indium Foil (0.1microns thick) supported by Ni mesh acts as UV filter cutting off transmission above 1100A
  - Carbon contamination of filters significantly degraded performance
  - Filter design does not lend itself to traditional cleaning
- JPL post treatments yielded significant (>2X) improvement in filter transmission
  - Gentle, low-temperature process results in no degradation in kill ratio for Lyman-alpha
  - Indium filter integrity maintained
- ALD AR coating results demonstrate the feasibility of integrated UV filters directly on the detector itself



# UV Optical Coatings

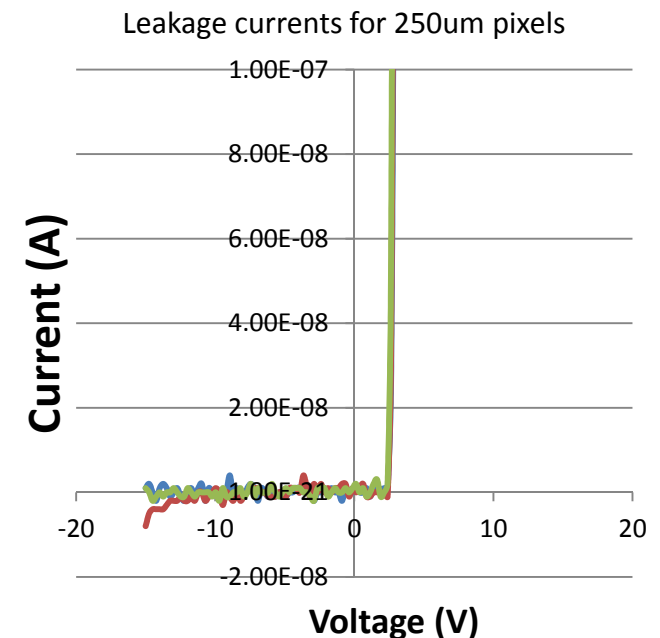
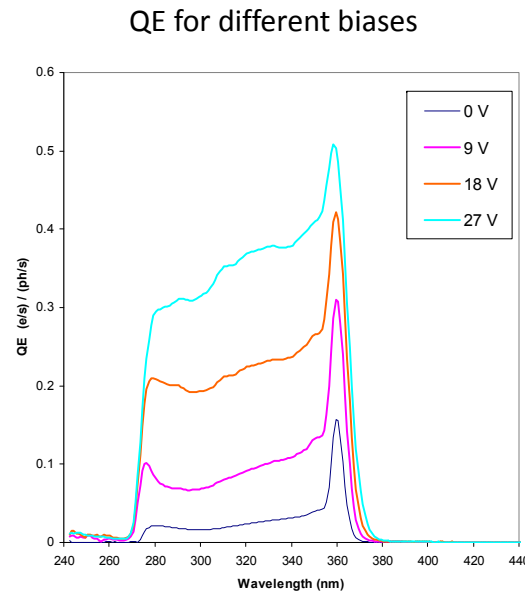
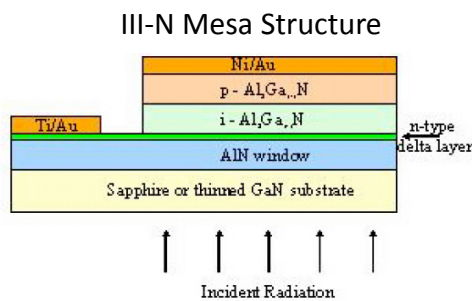
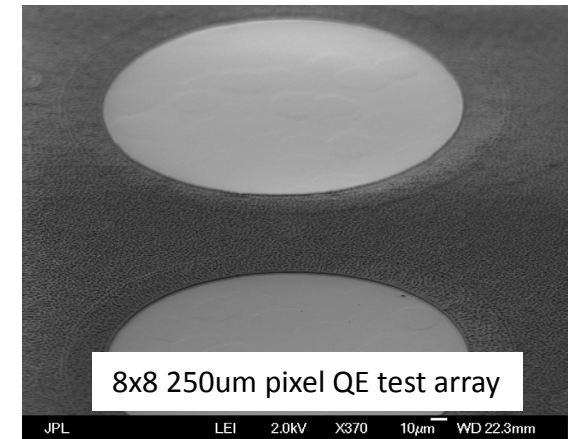
- Reflective coatings determine the mission architecture for any UV mission (FUSE, HST/COS, etc)
- FUV has a significant number of spectral lines that are of great interest to astronomers
- Aluminum mirrors require protective coatings (*i.e.* LiF or thick  $\text{MgF}_2$ ) to prevent oxidation which would otherwise destroy reflectivity in the FUV
- These coatings currently necessitate compromises on several levels
  - Polarization issues in Optical
  - Low efficiency in UV forces telescope designs with larger mirrors and separated into LiF and  $\text{MgF}_2$  channels to achieve desired sensitivity
- By using very thin, but high quality,  $\text{MgF}_2$ , both issues can be addressed simultaneously.
  - Very thin coatings minimize impact on polarization of incident light
  - Thin films of  $\text{MgF}_2$  (1-2nm) enable higher reflectivity (due to lower absorption losses) than LiF or thick  $\text{MgF}_2$
- Table below demonstrates some of the changes that FUSE would have had with better coatings



	Resolution	Aeff	Imaging?	Environmental	Size
FUSE	~20,000	~30 cm <sup>2</sup> /channel from 1000 – 1180 ~10 cm <sup>2</sup> /channel from 900 - 1000	No.	Hygroscopic Coatings	~6 m
FUSE w/ improved coatings	>40,000	Simpler optical design @ 100 cm <sup>2</sup> From 900 - 1180 Angstroms	Yes.	Not hygroscopic	~3 m

# ALD for III-N Detectors

- III-N APD detectors are also useful for UV detection
  - Inherently solar blind to prevent unintended response to visible light
  - Gain factors of 100 or more reported
- High bias required for enhanced gain factors
- Current detectors limited by dark current, but surface passivation (*i.e.* ALD) can be utilized to improve signal to noise



# Conclusions

- Benefits of ALD for UV instruments and application
  - Ultrathin, highly conformal, and uniform films over arbitrarily large surface area
  - High quality films (density, roughness, conductivity, *etc.*)
  - Angstrom level control of stoichiometry, interfaces, and surface properties
    - Multilayer nanolaminates/nanocomposites
    - Low temperature surface engineering
- UV flight applications enabled by ALD
  - Anti-reflective coatings/Mirrors/Filters/Optics for UV/Vis/NIR Detectors
  - Surface Passivation for III-N detectors



# Acknowledgements

- UV Filters/Mirrors
  - M. Beasley, B. Gantner (U. Colorado CASA)
- III-N Detectors
  - Doug Bell (JPL) and S. Shahedipour, et al (SUNY-Albany CNSE)
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